

**Amendments to the Abstract of the Disclosure:**

**Please delete the Abstract of the Disclosure in its entirety and substitute the following therefor:**

A multistate magnetorestrictive random access memory unit (MRAM) includes a plurality of memory cells, with each of the cells being written to and read from independently of other cells. The plurality of memory cells includes a recording layer as a pinned magnetic layer and a read layer as an unpinned layer. The unpinned layer has a higher Curie point than the pinned layer. The pinned layer in an individual cell is heated to near its Curie point and a bit line current and a word line current are used to align the magnetization vector of the recording layer at a plurality of angles relative to the magnetization vector of the read layer.